Preparation of piezoelectric PZT micro-discs by sol-gel method

This paper describes a modified sol-gel method to prepare PZT discs of nearly 1 µm thickness without repeating any process. The method is based on the subdivision of the PZT precursor into small areas prior to sintering. The subdivision is realised by pouring the precursor solution into a ZnO mold. Ultrasonic transducers were fabricated using the PZT disc and the piezoelectricity of the PZT disc in GHz ranges were discussed.

Keywords: PZT, sol-gel method, ultrasonic transducer, piezoelectricity

1. Introduction

Because of its very large electromechanical coupling factor, lead zirconate titanate (PZT) ceramics has widely been used as ultrasonic transducers and actuators. Presently, PZT films are extensively investigated for device miniaturisation, enhanced device performance and integration with semiconductor circuitry (1).

Various techniques such as sputtering (2) (3) and MOCVD (4) have been applied to the PZT film deposition. Amongst them, sol-gel method (5), deposition process of which is very simple, is one of the most attractive techniques; PZT films with highly piezoelectric properties can be prepared by the method. In fact, PZT films deposited by the sol-gel method have successfully been applied to develop ultrasonic devices operating in UHF and SHF ranges (6) (7), where mechanically thinned ceramic plates are of no use.

One of the drawbacks of the sol-gel method is that the film thickness obtained by a single batch is limited to circa 0.1 µm, which means that both spin-coating and prebaking processes should be repeated (see Fig. 1) for preparing thicker films. This drawback originates from a large internal stress induced in the film during heating process; the residual stress causes cracks and limits the film thickness to about 1 µm resulting in poor productivity of the films.

To deal with this problem, lateral relaxation of the internal stress has been proposed, in which thin PZT precursor layer is subdivided into small areas prior to the heating process (8); for high frequency applications, the required area for PZT films is usually very small. For example, Ref. (9) demonstrated that crack-free PZT films of nearly 1 µm thickness can be deposited in a single step by subdividing a thick PZT precursor with chemical etching. Although the films showed strong piezoelectricity, they were not reproducible because the film thickness varies widely; it is difficult to spin-coat PZT solution of sufficient thickness onto a flat surface.

This paper describes another approach to prepare thick PZT films by the sol-gel method, where PZT precursor is subdivided by a procedure similar to the lift-off process; PZT precursor solution is poured into a mold fabricated by a sputter-deposited ZnO film, which is removed after the heating process.

In the following sections, the fabrication process is described in detail and ultrasonic properties of the fabricated films are discussed.

2. Preparation of PZT micro-discs

Figure 2 shows the modified preparation process for the PZT films.

First, a Pt/Ti layer is deposited on a Si substrate as a buffer layer, which prevents Pb ions from diffusing into the Si substrate as well as accelerates the crystallisation of PZT films. The Pt/Ti layer also acts as a bottom electrode for the ultrasonic transducers described later. A ZnO film is sputter-deposited on the Pt/Ti layer (Fig. 2 (1) (2)).

Secondly, an array of pits, which acts as a mold for PZT precursor solution, is formed in the ZnO film by
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Fig. 2. Modified preparation process of PZT films.

conventional photolithography using an acetic acid solution (33wt%) as an etchant (Fig. 2 (3) ∼ (4)). In the present experiment, the thickness and diameter of each pit are 1.2 µm and 200 µm, respectively.

Thirdly, PZT precursor solution is poured into the ZnO mold by spin-coating (Fig. 2 (5)). As the solution, CFP-1\textsuperscript{1(10)} of Kanto Chemical Co., Inc. (nominal composition; Pb/Zr/Ti = 105 : 52 : 48) was employed.

After drying, the precursor gel is etched along the rims of the ZnO mold (Fig. 2 (6) ∼ (7)) to prevent the precursor and ZnO mold from chemically reacting. The patterning for the gel etching is performed by conventional photolithography, where OMR83 of Tokyo Ohka Kogyo Co., Ltd. was used as a photoresist because of its chemical stability against alcohol. As an etchant, the solvent for the precursor solution, 2-methoxyethanol (CH\textsubscript{3}O(CH\textsubscript{2})\textsubscript{2}OH), was employed\textsuperscript{9}.

Figure 3 shows thus fabricated and prebaked PZT discs at 450°C for 60 min. Gaps are clearly seen between the precursor and the mold although the centre of each disc does not exactly agree with that of the mold.

After prebaking, the ZnO mold is removed by acetic acid solution (Fig. 2 (9)). Note that the resist layer burns and disappears during the prebaking process.

Finally, the precursor discs are sintered at 650°C for 60 min. in O\textsubscript{2} ambient gas (Fig. 2 (10)).

Figure 4 shows the sintered PZT discs, for which the rim-etching procedure (Fig. 2 (6) ∼ (7)) was omitted; around the PZT discs, one can see some residua which are resistant to acetic acid solution.

XRD analysis showed that the discs contain ZnO-derived compounds, while the residua contain PZT-derived compounds as shown in Table 1. This means that the thermal diffusion occurred during the prebaking process leaving the residua.

<table>
<thead>
<tr>
<th>without rim-etching process</th>
<th>residua (ZnO region)</th>
<th>proposed method (ZnO region)</th>
<th>PZT disc region</th>
</tr>
</thead>
<tbody>
<tr>
<td>PZT</td>
<td>ZnO</td>
<td>PbTiO\textsubscript{2}</td>
<td></td>
</tr>
<tr>
<td>ZnPbO\textsubscript{x}</td>
<td>PbTiO\textsubscript{2}</td>
<td></td>
<td></td>
</tr>
<tr>
<td>ZnTiO\textsubscript{x}</td>
<td>ZnTiO\textsubscript{2}</td>
<td></td>
<td></td>
</tr>
<tr>
<td>PbO\textsubscript{x}</td>
<td>PbO\textsubscript{x}</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

Figure 5 shows the sintered PZT discs, for which all the processes shown in Fig. 2 are applied (without omitting the rim-etching procedure (Fig. 2 (6) ∼ (7))). By applying the rim-etching procedure, it is seen that no
residue is left. In addition, no ZnO-derived compound was detected by XRD analysis. Hence, it is concluded that the diffusion problem is completely avoided by the rim-etching procedure.

The thickness of the fabricated PZT disc was about 0.7 µm. Although cracks are still observed on a surface, they may be removed by reducing the disk area a little bit more.

![Fig. 5. Fabricated arrayed PZT discs by the present method.](image)

The fabrication process is summarised in Table 2.

<table>
<thead>
<tr>
<th>Substrate</th>
<th>Pt/Ti/Si</th>
</tr>
</thead>
<tbody>
<tr>
<td>PZT precursor solution</td>
<td>CFP-1 (Kanto Chemical Co., Inc.)</td>
</tr>
<tr>
<td>Pb : Zr : Ti</td>
<td>105 : 52 : 48</td>
</tr>
<tr>
<td>Etchant</td>
<td>2-methoxyethanol</td>
</tr>
<tr>
<td>for PZT precursor</td>
<td>(CH₃O(CH₂)₂OH)</td>
</tr>
<tr>
<td>Drying</td>
<td>150°C 30 min.</td>
</tr>
<tr>
<td>Prebaking</td>
<td>450°C 60 min.</td>
</tr>
<tr>
<td>Sintering</td>
<td>650°C 60 min.</td>
</tr>
</tbody>
</table>

### 3. Piezoelectricity

Piezoelectricity of the PZT discs is discussed by fabricating ultrasonic transducers, where a top Al electrode is fabricated using the lift-off technique. The PZT disc transducer behaviour was characterised by observing ultrasonic pulse echo trains reflected at the bottom surface of the Si substrate. The measurement system and the transducer configuration used in the experiment are shown in Figs. 6 and 7 respectively, where the PZT disc transducer is polarised by superimposing DC bias on RF signals.

Figure 8 shows the observed pulse echo responses in the time domain, where the bias voltage \( V_B \) is fixed at 15 V. By the Fourier transform of the first pulse echo observed in the time domain, the frequency response of the insertion loss was obtained as shown in Fig. 9.

The minimum insertion loss of 45.2 dB is obtained at \( f = 2.2 \) GHz, clearly showing the piezoelectricity of the PZT disc in GHz ranges. The measured minimum loss was about 10 dB larger than that estimated using material constants for PZT-5H bulk materials \(^{(11)}\). The increase in the minimum insertion loss may be due to the ohmic loss of a bottom Pt/Ti electrode.

![Fig. 6. Measurement system.](image)

![Fig. 7. PZT transducers under testing.](image)

![Fig. 8. Ultrasonic pulse echo trains. (DC bias : \( V_B = 15V \))](image)

### 4. Conclusion

This paper described a modified sol-gel method to prepare PZT discs of nearly 1 µm thickness without repeating any process. The method is based on the subdivision of the PZT precursor into small areas prior to sintering. The subdivision is realised by pouring the precursor solution into a ZnO mold. It was also shown that etching of the precursor gel along the rims of the ZnO mold is effective in preventing the precursor and
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ZnO mold from chemically reacting each other. Ultrasonic transducers were fabricated using the PZT disc and the piezoelectricity of the PZT disc in GHz ranges were discussed.

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References


Tatsuya Omori (Non-member) was born on 1 April 1967. He received his B.Eng. degree in electronics engineering in 1989 from Kogakuin University, and M.Eng. degree and Ph.D. (Eng.) degree in 1991 and 1994, respectively, from Chiba University. He joined Fujikura Co. Ltd. in 1994 and he engaged in research and development of optical fibre cable and LCX. He has been employed in Chiba University as a research associate since 1998. His current research includes optical fibre sensors, SAW device design and preparation of piezoelectric thin films and their applications.

Hirofumi Makita (Non-member) received his BS degree in 1997 from the University of Electro-Communications, and M.Eng. degree in 1999 from Chiba University. He joined Aloka Co. Ltd. in 1999 and he engaged in research and development of digital imaging technology for diagnostic ultrasound systems.

Mutsumi Takamatsu (Non-member) was born on 2 August 1975. He received his B.Eng. and M.Eng. degree in 1998 from Chiba University. He joined AIWA Co. Ltd. in 1999.

Ken-ya Hashimoto (Member) received his BS and MS degrees in electrical engineering in 1978 and 1980, respectively, from Chiba University, and Dr. Eng. degree from Tokyo Institute of Technology in 1989. In 1980, he joined Chiba University as a Research Associate, and is now Associate Professor of the University. In 1998, he was a Visiting Professor at Helsinki University of Technology, In winter 1998/1999, he was a Visiting Scientist of the Laboratoire de Physique et Metrologie des Oscillateurs (LPMO), CNRS, France, and in 1999 and 2001, he was a Visiting Professor at the University of Linz, Austria. His current research include various type of surface and bulk acoustic wave devices, acoustic wave sensors, and application of thin film micro-machining technologies to the acoustic wave devices. He has been active in the areas of surface acoustic wave devices, ultrasonic transducers, piezoelectric thin films, and their sensor and/or actuator applications.
Masatsune Yamaguchi (Member) was born on 15 September 1944. He received BS degree in Electrical Engineering in 1967 from Nagoya Institute of Technology, and MS and Dr. Engrg. degrees in Electrical Engineering in 1969 and 1972, respectively, from Tokyo Institute of Technology. He joined Chiba University as Research Assistant in 1972 and became Associate Professor in 1975. After he worked as Research Assistant in Oxford University, UK, he was promoted as Professor of Electrical and Electronics Engineering in Chiba University in 1987. He also served as Director of University Computer centre (1992-1996) and University Library (1996-1998), and is now Dean of Faculty of Engineering, Chiba University. He has worked surface and bulk acoustic wave devices, piezoelectric thin films and sensor devices over the past thirty years.

Manabu Sato (Non-member) received a B.E. degree in material from Nagoya Institute Of Technology in 1983. In 1983, he joined NGK Spark Plug Co., LTD, Nagoya, Japan, where he was engaged in the dielectric ceramics. He is presently an assistant manager at Research and Development Center, working on dielectric and LTCC materials.